

L Number	Hits	Search Text	DB	Time stamp
1	41	(257/645).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 17:26
2	2	((257/645).CCLS.) and trap with (density carrier impurity holes electron) same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 16:45
3	182	(257/\$).ccls. and trap with (density carrier impurity holes electron) same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 17:02
4	154	control with gate and trap with (density carrier impurity holes electron) same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 17:01
5	83	(control with gate and trap with (density carrier impurity holes electron) same nitride) not ((257/\$).ccls. and trap with (density carrier impurity holes electron) same nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 17:02
6	3	5907183.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 17:27
7	3	5731238.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 17:27
-	18	insulation with layer with trap with density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 10:55
-	5	floating adj gate with trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 12:02
-	6	("4154873" "4331709" "4447272" "5010024" "5017979" "5019533").PN.	USPAT	2002/05/10 16:23
-	135	(silicon adj oxide silicon adj nitride insulating insulator flating adj gate control adj gate ONO NON)with trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 12:20
-	26	silicon adj nitride with trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 14:38
-	8	silicon adj nitride with trap adj density same hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 14:38
-	3	5731238.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 11:02

-	174	hydrogen with NON with insulating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:04
-	2	(hydrogen with NON with insulating) and floating with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:03
-	31	(hydrogen with NON with insulating) and nitride with hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:07
-	82	silicon with nitride with hydrogen and floating with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:18
-	7	("4688078" "4788082" "5256205" "5356672" "5356673" "5368897" "5403399").PN.	USPAT	2002/05/13 11:14
-	3	5483097.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:39
-	4	5483097.URPN.	USPAT	2002/05/13 11:18
-	1009419	silicon adj nitride wiht density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:43
-	33960	(silicon adj nitride wiht density) and (257/\$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:40
-	43257	(silicon adj nitride wiht density) and inter ajd layer and floating with gate and (257/\$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:41
-	95	(silicon adj nitride wiht density) and inter adj layer and floating with gate and (257/\$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:43
-	2498	silicon adj nitride with density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:43
-	1	(silicon adj nitride with density) and inter adj layer and floating with gate and (257/\$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:44
-	32	(silicon adj nitride with density) and floating with gate and (257/\$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 11:49
-	63	silicon adj nitride adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 12:10

-	8	thermal with nitr\$8 same trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 12:12
-	8	thermal with nitr\$ same trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 12:13
-	0	thermal with nitrization same trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 12:14
-	0	thermal with nitrization and trap adj density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 12:14
-	30	thermal with nitrization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 16:41